

what is claimed is :

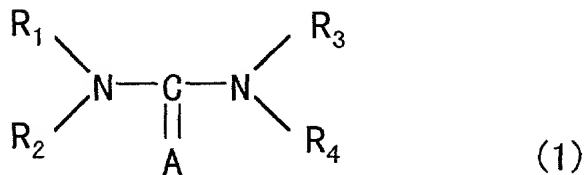
1. A stripper composition containing an anticorrosive agent which contains (a) urea or a urea derivative and (b) a hydroxy aromatic compound, as essential components.

2. A stripper composition according to Claim 1, further comprising:

(c) a hydroxylamine or an alkanolamine, and
(d) water.

3. A stripper composition according to Claim 2, wherein the amounts of the components (a), (b), (c) and (d) are 1 to 60% by mass, 0.1 to 20% by mass, 5 to 70% by mass and 2 to 40% by mass, respectively.

4. A stripper composition according to Claim 1, wherein the component (a) is a compound represented by the following general formula (1):



5 (R₁, R₂, R₃ and R₄ are each independently a hydrogen atom or an alkyl group having 1 to 3 carbon atoms; and A is an oxygen atom or a sulfur atom).

5. A stripper composition according to Claim 1, wherein the component (b) is a benzene derivative having at least two phenolic hydroxyl groups in the molecule.

6. A stripper composition according to Claim 5, wherein the component (b) is at least one compound selected from the group consisting of pyrogallol, hydroxyhydroquinone, fluoroglucinol, gallic acid and
5 tannic acid.

7. A stripper composition according to Claim 1, removing a resist film and/or an etching residue on a semiconductor substrate having an exposed metal film.

8. A stripper composition according to Claim 7, wherein the metal film is a copper film.

9. A stripping method which comprises stripping a resist film and/or an etching residue on a semiconductor wafer having an exposed metal film, by using a stripper composition according to Claim 1.

10. A stripping method which comprises stripping a resist film and/or an etching residue on a semiconductor wafer having an exposed metal film, by using a stripper

composition according to Claim 2.

11. A stripping method which comprises stripping a resist film and/or an etching residue on a semiconductor wafer having an exposed metal film, by using a stripper composition according to Claim 3.

12. A stripping method which comprises stripping a resist film and/or an etching residue on a semiconductor wafer having an exposed metal film, by using a stripper composition according to Claim 4.

13. A stripping method which comprises stripping a resist film and/or an etching residue on a semiconductor wafer having an exposed metal film, by using a stripper composition according to Claim 5.

14. A stripping method which comprises stripping a resist film and/or an etching residue on a semiconductor wafer having an exposed metal film, by using a stripper composition according to Claim 6.

15. A stripping method which comprises:
forming, on a semiconductor wafer, a metal
film and an insulating film in this order;
forming a resist film thereon;

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5 conducting dry etching with the resist film
being used as a mask, to form, in the insulating film,
dents reaching the metal film; then
stripping the resist film and/or the residue
of etching by using a stripper composition according to
10 Claim 1.

16. A stripping method which comprises:
forming, on a semiconductor wafer, a metal
film and an insulating film in this order;
forming a resist film thereon;
5 conducting dry etching with the resist film
being used as a mask, to form, in the insulating film,
dents reaching the metal film; then
stripping the resist film and/or the residue
of etching by using a stripper composition according to
10 Claim 2.

17. A stripping method which comprises:
forming, on a semiconductor wafer, a metal
film and an insulating film in this order;
forming a resist film thereon;
5 conducting dry etching with the resist film
being used as a mask, to form, in the insulating film,
dents reaching the metal film; then
stripping the resist film and/or the residue

of etching by using a stripper composition according to
10 Claim 3.

18. A stripping method which comprises:
forming, on a semiconductor wafer, a metal
film and an insulating film in this order;
forming a resist film thereon;
5 conducting dry etching with the resist film
being used as a mask, to form, in the insulating film,
dents reaching the metal film; then
stripping the resist film and/or the residue
of etching by using a stripper composition according to
10 Claim 4.

19. A stripping method which comprises:
forming, on a semiconductor wafer, a metal
film and an insulating film in this order;
forming a resist film thereon;
5 conducting dry etching with the resist film
being used as a mask, to form, in the insulating film,
dents reaching the metal film; then
stripping the resist film and/or the residue
of etching by using a stripper composition according to
10 Claim 5.

20. A stripping method which comprises:

forming, on a semiconductor wafer, a metal film and an insulating film in this order;

forming a resist film thereon;

5 conducting dry etching with the resist film being used as a mask, to form, in the insulating film, dents reaching the metal film; then

stripping the resist film and/or the residue of etching by using a stripper composition according to

10 Claim 6.

21. A stripping method which comprises:

forming, on a semiconductor wafer, a metal film, a first insulating film and a second insulating film having desired openings;

5 conducting dry etching with the second insulating film being used as a mask, to form, in the first insulating film, dents reaching the metal film; then

stripping the residue of etching by using a
10 stripper composition according to Claim 1.

22. A stripping method which comprises:

forming, on a semiconductor wafer, a metal film, a first insulating film and a second insulating film having desired openings;

5 conducting dry etching with the second

insulating film being used as a mask, to form, in the first insulating film, dents reaching the metal film; then

stripping the residue of etching by using a
10 stripper composition according to Claim 2.

23. A stripping method which comprises:

forming, on a semiconductor wafer, a metal film, a first insulating film and a second insulating film having desired openings;

5 conducting dry etching with the second insulating film being used as a mask, to form, in the first insulating film, dents reaching the metal film; then

stripping the residue of etching by using a
10 stripper composition according to Claim 3.

24. A stripping method which comprises:

forming, on a semiconductor wafer, a metal film, a first insulating film and a second insulating film having desired openings;

5 conducting dry etching with the second insulating film being used as a mask, to form, in the first insulating film, dents reaching the metal film; then

stripping the residue of etching by using a

10 stripper composition according to Claim 4.

25. A stripping method which comprises:

forming, on a semiconductor wafer, a metal film, a first insulating film and a second insulating film having desired openings;

5 conducting dry etching with the second
insulating film being used as a mask, to form, in the
first insulating film, dents reaching the metal film;
then

stripping the residue of etching by using a
10 stripper composition according to Claim 5.

26. A stripping method which comprises:

forming, on a semiconductor wafer, a metal film, a first insulating film and a second insulating film having desired openings;

5 conducting dry etching with the second
insulating film being used as a mask, to form, in the
first insulating film, dents reaching the metal film;
then

stripping the residue of etching by using a
10 stripper composition according to Claim 6.

27. A stripping method according to Claim 9,
wherein the metal film is a copper film.

28. A stripping method according to Claim 10,
wherein the metal film is a copper film.

29. A stripping method according to Claim 11,
wherein the metal film is a copper film.